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## MCP6002T-E/SN(MS)

**Product specification** 





#### **GENERAL DESCRIPTION**

The MCP6002T-E/SN(MS) is dual CMOS operational amplifier that uses the proprietary auto-calibration technique to simultaneously provides very lowoffset voltage, near-zero drift over time and temperature. These miniature, high-precision, low quiescent current amplifiers offer high-impedance inputs that have a common-mode range 200mV beyond the rails, and rai-to-rail output that swings within 50mV of the rails, single or dual supplies as low as 2.1V(±1.35 V) and up to 5.5V(±2.75V) can be used. These devices are optimized for low voltage, single supply operation.

The MCP6002T-E/SN(MS) offers excellent CMRR without the crossover associated with traditional complementary in nput stages. This design results in superior performance for driving analog-to-digital converters (ADC) without degrad ation of differential linearity. The MCP6002T-E/SN(MS) is available in the 8-pin VSSOP and TSSOP packages.

#### **FEATURES**

- VDD range:2.1V to 5.5V
- Low Offset Voltage:0.5mV (Typical)
- Low Drift:0.65μV/C(Typical)
- Low Noise
- Quiescent Current:50μA (Total)
- Rail to Rail Input/Output
- MicroSize Packages:SOP-8

#### **APPLICATIONS**

- Transducers
- Temperature Measurement
- Electronic Scales
- Medical instrumentation
- Handheld Test Equipment

## **Reference News**

PACKAGE OUTLINE	PIN CONFIGURATION	Marking
SOP-8	10UT	MCP6002E SN@3**  MSKSEMI

#### PIN DESCRIPTION

Pin Name	Pin Number	Description
10UT	1	Output 1
1IN-	2	Inverting input 1
1IN+	3	Noninverting input 1
GND	4	Negative(lowest)power supply
2IN+	5	Noninverting input 2
2IN-	6	Inverting input 2
2OUT	7	Output 2
Vcc+	8	Positive(highest)power supply



## **SIMPLIFIED SCHEMATIC**

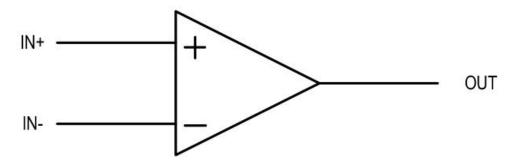


Figure 1.Simplified Schematic

## **ABSOLUTE MAXIMUM RATINGS**

Thermal Resistance θ Jc	130°℃/W
Supply Voltage	2.1to 5.5V
Signal Input Terminals Voltage	0.1 to (V+)+0.1V
Operating Junction Temperature	150℃
Operating Temperature Range	55°C to 125°℃
Storage Temperature	65°C to 150°C



## **ELECTRICAL CHARACTERISTICS**

(AtTa=25  $^{\circ}\text{C}$  ,RL=10k to Vs/2,and Vour=Vs/2,unless

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Input Offset Voltage	$Vs=\pm 2.5V$	-2	0.5	2	mV
nput Offset Voltage Drift	TA=-55℃ to 125℃		0.65		μV/°C
Power Supply Rejection Ratio	Vs =2.1V to 5.5V TA=-55°C to 125°C	80	90		dB
Input Bias Curren	TA=25℃		2		pA
Input Offset Curren			1		pA
Common-mode Voltage Range		(V-)-0.1		(V+)+0. 1	V
Common-mode Rejectior Ratio	(V-)-0.1 <vcm<(v+)+0.' TA=-55℃ to 125℃</vcm<(v+)+0.' 	80	95		dB
Open Loop Voltage Gain	(V-)+100mV <vo<(v+)-10 0mv<br="">RL=10k TA=-55°Cto125°C</vo<(v+)-10>	80	100		dB
Gain-bandwidth product	CL=120pF		1.5		MHz
Slew Rate	G=+1		1.2		V/μs
Specified Voltage Range		2.1		5. 5	V
Quiescent Current (Total)	1o=0A		50		μА
Operating Temperature Range		-55		125	$^{\circ}$
Storage Temperature Range		-65		150	$^{\circ}$



#### TYPICAL PERFORMANCE CHARACTERISTICS



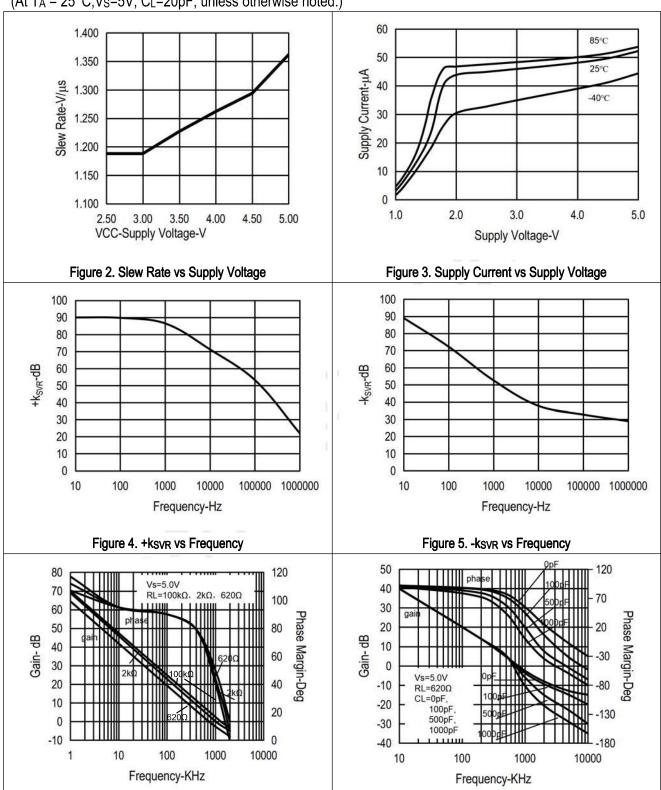
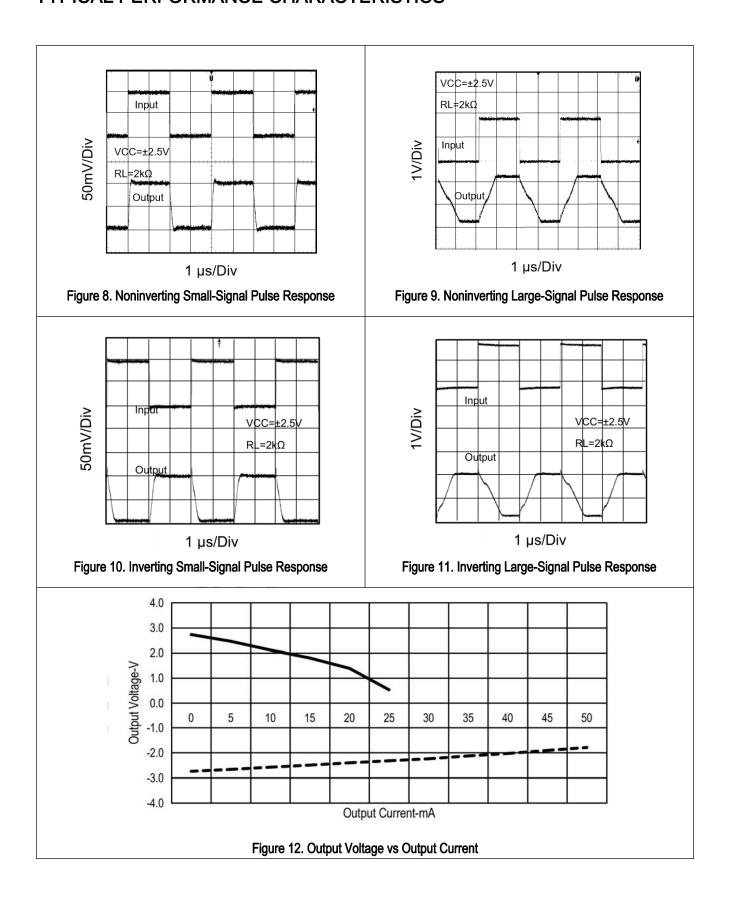


Figure 6. Frequency Response vs Resistive Load

Figure 7. Frequency Response vs Capacitive Load



## TYPICAL PERFORMANCE CHARACTERISTICS





#### **FUNCTIONAL DESCRIPTION**

#### **Operating Voltage**

The MCP6002T-E/SN(MS) device is fully specified and ensured for operation from 2.1V to 5.5V.In addition,many specifications apply from -55°C to 125°C. Parameters that vary significantly with operating voltages or temperature are shown in the Typical Characteristics graphs

#### **Unity-Gain Bandwidth**

The unity-gain bandwidth is the frequency up to which an amplifier with a unity gain may be operated without greatly distorting the signal. The MCP6002T-E/SN(MS) device has a 1.5-MHz unity-gain bandwidth.

#### Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. The MCP6002T-E/SN(MS) devices have a 1.2-V/ $\mu$  s slew rate. The MCP6002T-E/SN(MS) is characterized to perform with this technique; the recommended resistor value is approximately 20 k.

#### **Device Functional Modes**

The MCP6002T-E/SN(MS) device has a single functional mode. The device is powered on as long as the power supply voltage is between 2.1V(±1.35V)and 5.5V(±2.75V).

#### APPLICATIONS INFORMATION

The MCP6002T-E/SN(MS) is a unity-gain stable, precision operational amplifier with very low offset voltage drift; these devices are also free from output phase reversal. Applications with noisy or high-impedance power supplies require decoupling capacitors close to the device power-supply pins. In most cases, 0.1 µF capacitors are adequate.

#### **Typical Application**

Figure 13 shows a simple circuit to convert a single-ended input into differential output. The MCP6002T-E/SN(MS) could be used to build this circuit. The circuit is composed of two amplifiers. One amplifier acts as a buffer and creates a voltage, Vour+. The second amplifier inverts the input and adds a reference voltage to generate Vour-. Both Vour+ and Vour-range from 0.5 to 2V. The difference, VDIFF, is the difference between VouT+ and VouT-.

#### **Detailed Design Procedure**

Linearity over the input range is key for good dc accuracy. The common mode input range and the output swing limitations determine the linearity. In general, an amplifier with rail-to-rail input and output swing is required. Bandwidth is a key concern for this design. Because MCP6002T-E/SN(MS) has a bandwidth of 1 MHz, this circuit will only be able to process signals with frequencies of less than 1 MHz.

Because the transfer function of Vour-is heavily reliant on resistors(R1,R2,R3,and R4),use resistors with low tolerances to maximize performance and minimize error. This design used resistors with resistance values of 36 k with tolerances measured to be within 2%. If the noise of the system is a key parameter, the user can select smaller resistance values (6 k or lower) to keep the overall system noise low. This ensures that the noise from the resistors is lower than the amplifier noise.



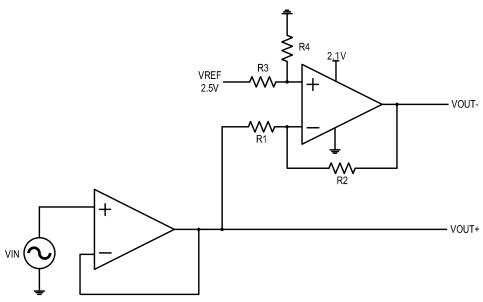
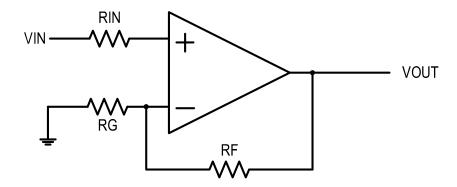


Figure 13. Schematic for Single-Ended Input to Differential Output Conversion

#### **LAYOUT**

Use good PCB layout practices for best operational performance of the device,including:

- Keep the length of input traces as short as possible.
- Run the input traces as far away from the supply lines as possible to reduce parasitic coupling.
- Place components close to device and to each other to reduce parasific capacitance and parasitic errors.
- Use low-ESR,ceramic bypass capacitors to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
- Grounding for analog and digital portions of circuitry separately to suppresse the noise.





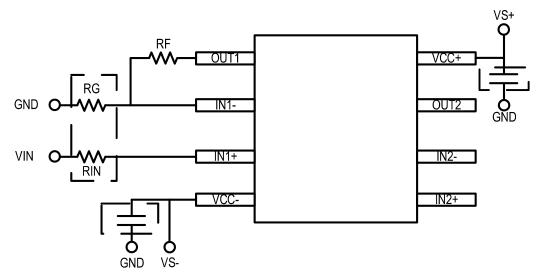
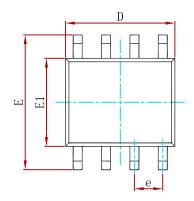
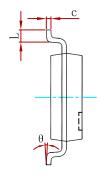


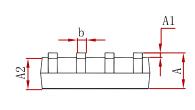
Figure 14. Operational Amplifier Schematic and Board Layout for Noninverting Configuration



## **PACKAGE MECHANICAL DATA**

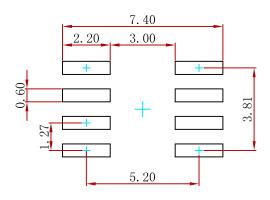






Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0. 250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0. 170	0. 250	0.007	0.010
D	4.800	5. 000	0. 189	0. 197
e	1. 270	(BSC)	0.050	(BSC)
E	5. 800	6. 200	0. 228	0. 244
E1	3.800	4.000	0. 150	0. 157
L	0.400	1. 270	0.016	0.050
θ	0°	8°	0°	8°

## **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MCP6002T-E/SN(MS)	SOP-8	2500PCS



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